

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	998226	(insulat\$3 dielectric)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/04 18:13
L2	147347	L1 and gate	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/04 18:13
L3	95659	L2 and (etch\$3 pattern\$4)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/04 18:13
L4	90648	L3 and (via contact open\$3 hole trench)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/04 18:13
L5	58014	L4 and (dop\$3 implant\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/04 18:13
L6	9162	L5 and plug	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/04 18:13
L7	8251	L6 and (source drain)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/04 18:13
L8	170	L7 and ((impurity concentration) near10 (high low) near10 plug)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/04 18:13
L9	1096274	(insulat\$3 dielectric)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/04 18:16
L10	89421	L9 and gate	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/04 18:16
L11	28533	L10 and (etch\$3 pattern\$4)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/04 18:16
L12	14100	L11 and (via contact open\$3 hole trench)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/04 18:16
L13	4469	L12 and (dop\$3 implant\$3)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/04 18:16
L14	0	L13 and plug	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/04 18:16

L15	10375	two near5 layer\$3 near5 contact	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/04 18:16
L16	6465	L15 and (insulat\$3 dielectric)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/04 18:16
L17	2325	L16 and gate	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/04 18:16
L18	1761	L17 and (dop\$3 implant\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/04 18:16